

ABSTRACT OF THE DISCLOSURE

Semiconductor elements composing a semiconductor device are formed on a semiconductor substrate. Wirings composed of copper or an alloy mainly composed of copper are formed in wiring
5 layers through interlayer insulation films to connect the semiconductor elements to each other. When the wirings are formed, a temperature of the wirings is held in a first temperature zone covering $\pm 40^{\circ}\text{C}$ of a temperature at which a stress migration is most accelerated.